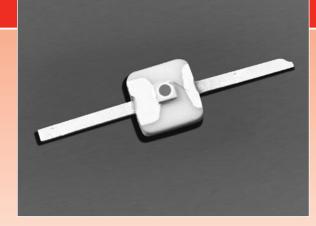
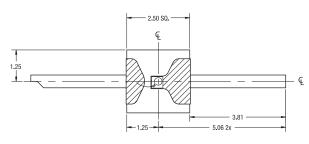
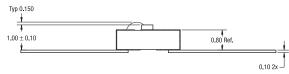
FCI-InGaAs-XXX-LCER

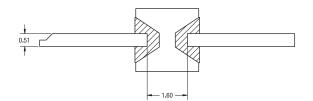
High Speed InGaAs Photodiodes Mounted on Ceramic Packages w/Leads

FCI-InGaAs-XXX-LCER with active area sizes of 70µm, 120µm, 300µm, 400µm and 500µm are part of OSI Optoelectronics's high speed IR sensitive photodiodes mounted on gull wing ceramic substrates. The chips can be epoxy/eutectic mounted onto the ceramic substrate.









Notes:

• All units in millimeters.

• All devices are mounted with low out gassing conductive epoxy with tolerance of ±25µm. Eutectic mounting is also available upon request.

APPLICATIONS

- High Speed Optical
- Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitoring
- Instrumentation

FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range
 - 900nm to 1700nm

Absolute Maximum Ratings PARAMETERS SYMBOL MIN MAX UNITS °C Storage Temperature T_{stg} -40 +85 Operating Temperature T_{op} 0 +70 °C Soldering Temperature T_{sld} ---+260 °C

		naracteristi conditions	FCI-InGaAs-70LCER			FCI-InGaAs-120LCER			FCI-InGaAs-300LCER			FCI-InGaAs-400LCER			T _A = FCI-InGaAs-500LCER			1
			MIN	TYP	MAX	MIN		MAX	MIN	TYP	MAX	MIN		MAX	MIN		MAX	UNITS
Active Area Diameter	AA _φ			70			120			300			400			500		μm
Responsivity	R _λ	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
		λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	Cj	V _R = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_{R} = 5.0V,$ $R_{L} = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Revervse Voltage					20			20			15			15			15	v
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz